

Dual P-channel MOSFET

ELM14817AA-N

General description

ELM14817AA-N uses advanced trench technology to provide excellent $R_{ds(on)}$ and low gate charge. Internal ESD protection is included.

Features

- $V_{ds} = -30V$
- $I_d = -8A$ ($V_{gs} = -20V$)
- $R_{ds(on)} < 18m\Omega$ ($V_{gs} = -20V$)
- $R_{ds(on)} < 21m\Omega$ ($V_{gs} = -10V$)
- ESD Rating : 1500V HBM

Maximum absolute ratings

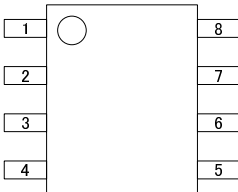
Parameter	Symbol	Limit	Unit	Note	
Drain-source voltage	V_{ds}	-30	V		
Gate-source voltage	V_{gs}	± 25	V		
Continuous drain current	I_d	$T_a = 25^\circ C$	-8.0	A	1
		$T_a = 70^\circ C$	-6.9		
Pulsed drain current	I_{dm}	-40	A	2	
Power dissipation	P_d	$T_a = 25^\circ C$	2.00	W	1
		$T_a = 70^\circ C$	1.44		
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$		

Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	$t \leq 10s$	$R\theta_{ja}$	50.0	62.5	$^\circ C/W$	1
Maximum junction-to-ambient	Steady-state		73.0	110.0	$^\circ C/W$	
Maximum junction-to-lead	Steady-state	$R\theta_{jl}$	31.0	40.0	$^\circ C/W$	3

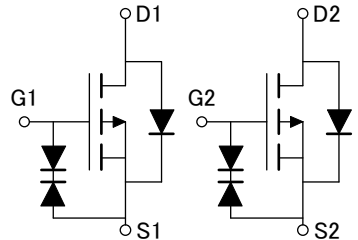
Pin configuration

SOP-8 (TOP VIEW)



Pin No.	Pin name
1	SOURCE2
2	GATE2
3	SOURCE1
4	GATE1
5	DRAIN1
6	DRAIN1
7	DRAIN2
8	DRAIN2

Circuit



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Electrical characteristics

T_a=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BV _{dss}	I _d =-250 μA, V _{gs} =0V	-30			V
Zero gate voltage drain current	I _{dss}	V _{ds} =-24V V _{gs} =0V			-1	μA
		T _j =55°C			-5	
Gate-body leakage current	I _{gss}	V _{ds} =0V, V _{gs} =±25V			±1	μA
Gate threshold voltage	V _{gs(th)}	V _{ds} =V _{gs} , I _d =-250 μA	-1.0	-2.8	-3.0	V
On state drain current	I _{d(on)}	V _{gs} =-10V, V _{ds} =-5V	-40			A
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =-20V I _d =-8A		14.1	18.0	mΩ
			T _j =125°C	20.0	25.0	
		V _{gs} =-10V, I _d =-8A		17.1	21.0	
		V _{gs} =-4.5V, I _d =-4A		44.0		mΩ
Forward transconductance	G _{fs}	V _{ds} =-5V, I _d =-8A		15		S
Diode forward voltage	V _{sd}	I _s =-1A, V _{gs} =0V			-1	V
Max. body-diode continuous current	I _s				-2.6	A
DYNAMIC PARAMETERS						
Input capacitance	C _{iss}			1760	2200	pF
Output capacitance	C _{oss}	V _{gs} =0V, V _{ds} =-15V, f=1MHz		360		pF
Reverse transfer capacitance	C _{rss}			255		pF
Gate resistance	R _g	V _{gs} =0V, V _{ds} =0V, f=1MHz		6.4	8.0	Ω
SWITCHING PARAMETERS						
Total gate charge	Q _g	V _{gs} =-10V, V _{ds} =-15V I _d =-8A		30	38	nC
Gate-source charge	Q _{gs}			7		nC
Gate-drain charge	Q _{gd}			8		nC
Turn-on delay time	t _{d(on)}			12.5		ns
Turn-on rise time	t _r	V _{gs} =-10V, V _{ds} =-15V		10.5		ns
Turn-off delay time	t _{d(off)}	R _l =1.8 Ω, R _{gen} =3 Ω		40.0		ns
Turn-off fall time	t _f			23.0		ns
Body diode reverse recovery time	t _{rr}	I _f =-8A, dI/dt=100A/μs		24	30	ns
Body diode reverse recovery charge	Q _{rr}	I _f =-8A, dI/dt=100A/μs		16		nC

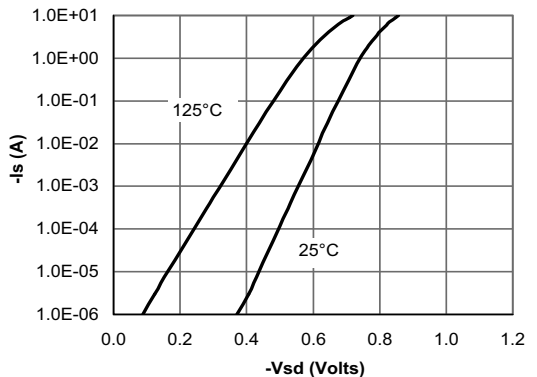
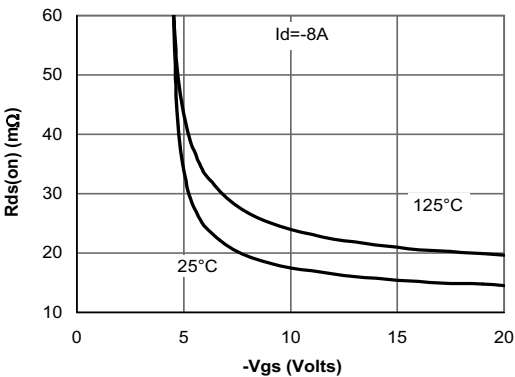
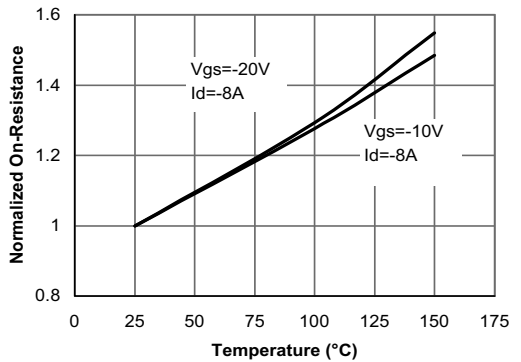
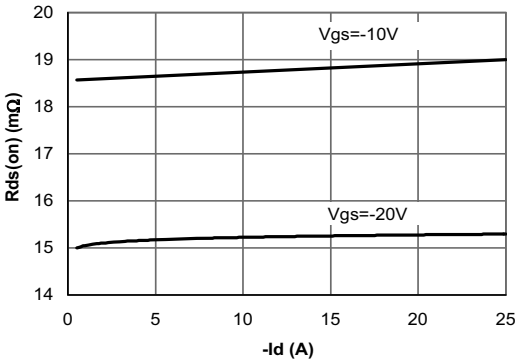
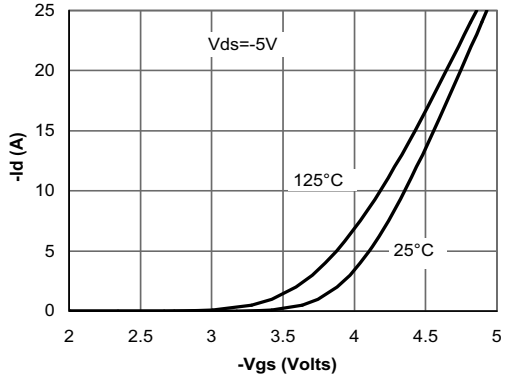
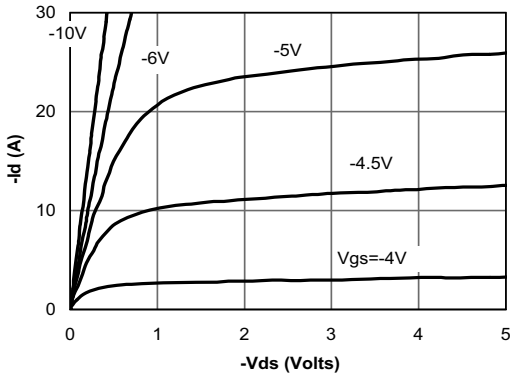
NOTE :

1. The value of R_{θja} is measured with the device mounted on 1in² FR-4 board of 2oz. Copper, in still air environment with T_a=25°C. The value in any given applications depends on the user's specific board design, The current rating is based on the t ≤ 10s thermal resistance rating.
2. Repetitive rating, pulse width limited by junction temperature.
3. The R_{θja} is the sum of the thermal impedance from junction to lead R_{θjl} and lead to ambient.
4. The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5%max.
5. These tests are performed with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_a=25°C. The SOA curve provides a single pulse rating.

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Typical electrical and thermal characteristics



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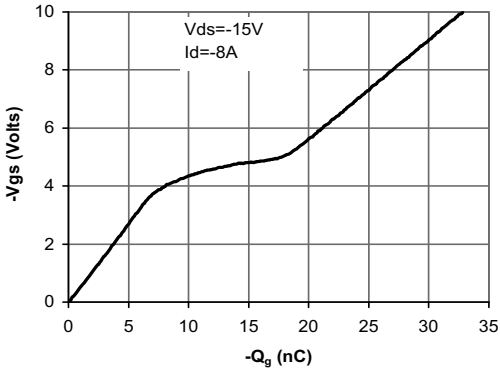


Figure 7: Gate-Charge Characteristics

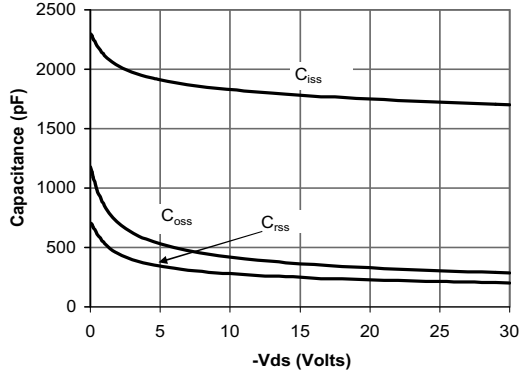


Figure 8: Capacitance Characteristics

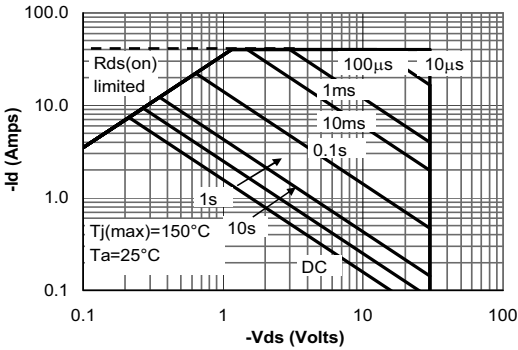


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

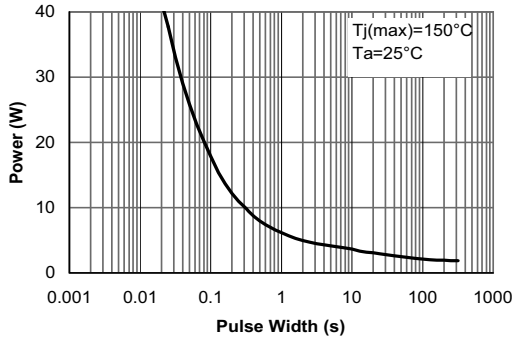


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

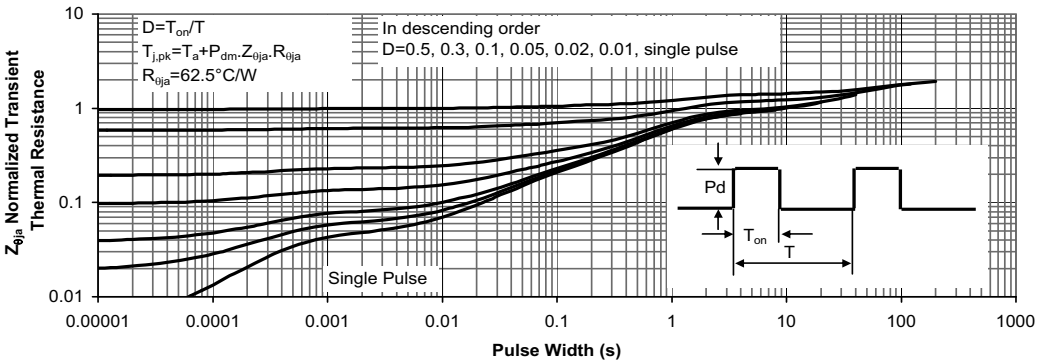


Figure 11: Normalized Maximum Transient Thermal Impedance